

BAS21TW

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BAS21TW

200mA Surface Mount Switching Diode Array 250V

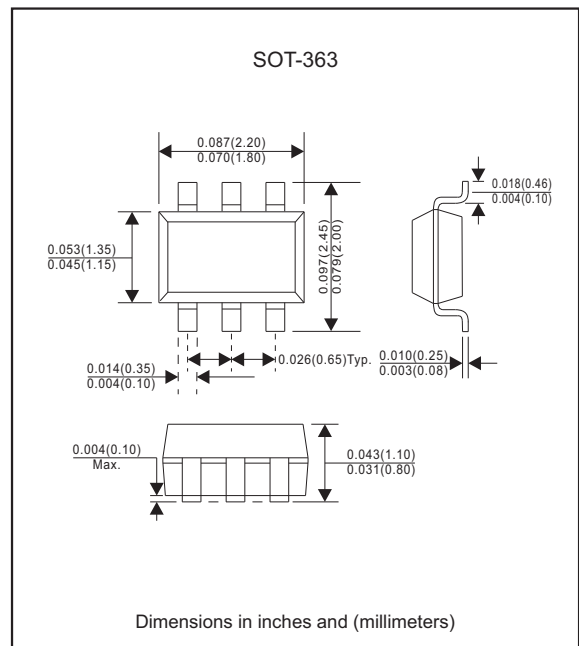
Features

- Fast speed switching
- For general purpose switching application
- High conductance
- Easily connected as full wave bridge
- Silicon epitaxial planar chip
- Lead-free parts meet RoHS requirements
- Suffix "-H" indicates Halogen-free part, ex. BAS21TW-H

Mechanical data

- Epoxy: UL94-V0 rated flame retardant
- Case : Molded plastic, SOT-363
- Terminals : Solder plated, solderable per MIL-STD-750, Method 2026
- Mounting Position : Any
- Weight : Approximated 0.006 gram

Package outline



Maximum ratings (AT $T_A=25^\circ\text{C}$ unless otherwise noted)

PARAMETER	Symbol	Value	UNIT
Non-repetitive peak reverse voltage	V_{RM}	250	V
Peak repetitive reverse voltage DC blocking voltage	V_{RRM} V_R	250	V
RMS reverse voltage	$V_{R(RSM)}$	177	V
Average rectified output current (Note 1, 3)	I_O	200	mA
Forward continuous current (Note 1)	I_{FM}	400	mA
Non-repetitive peak forward surge current @ $t = 1.0\mu\text{s}$ @ $t = 1.0\text{s}$	I_{FSM}	2.5 0.5	A
Thermal resistance junction to ambient (Note 1, 3)	$R_{\theta JA}$	556	$^\circ\text{C/W}$
Power dissipation (Note 1)	P_D	225	mW
Operating junction temperature range	T_J	+150	$^\circ\text{C}$
Storage temperature range	T_{STG}	-65 to +150	$^\circ\text{C}$

Electrical characteristics (AT $T_A=25^\circ\text{C}$ unless otherwise noted)

PARAMETER	Symbol	Min.	Max.	UNIT
Reverse breakdown voltage at $I_R = 100\mu\text{A}$	$V_{(BR)}$	250		V
Forward voltage (Note 2) at $I_F = 100\text{mA}$ at $I_F = 200\text{mA}$	V_F		1000 1250	mV
Reverse leakage current (Note 2) at $V_R = 200\text{V}$	I_R		1.0	μA
Diode capacitance, $V_R = 0\text{V}$, $f = 1.0\text{MHz}$	C_D		5.0	pF
Reverse recovery time ($I_F = I_R = 10\text{mA}$, $I_{rr} = 0.1 \times I_R$, $R_L = 100\Omega$)	t_{rr}		50	ns

Notes1. Device mounted on FR-4 PC board with recommended pad layout.
2. Short duration test pulse used to minimize self-heating effect.
3. One or more diodes loaded.

Rating and characteristic curves for each diode (BAS21TW)

Fig.1 FORWARD CHARACTERISTICS

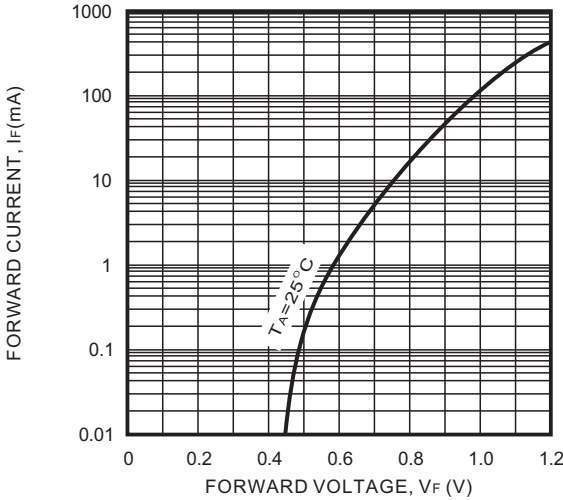


Fig.2 REVERSE CHARACTERISTICS

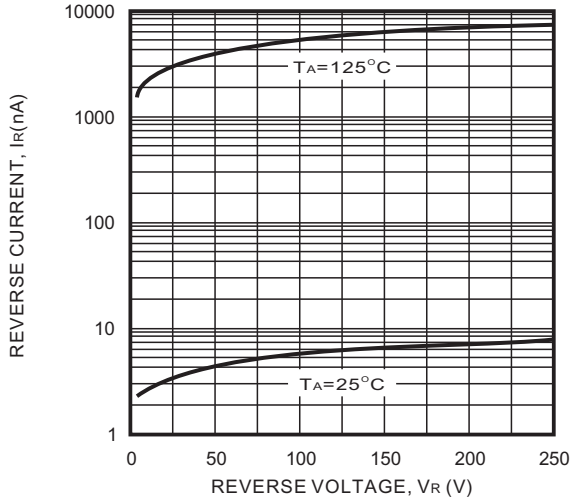


Fig.3 CAPACITANCE CHARACTERISTICS

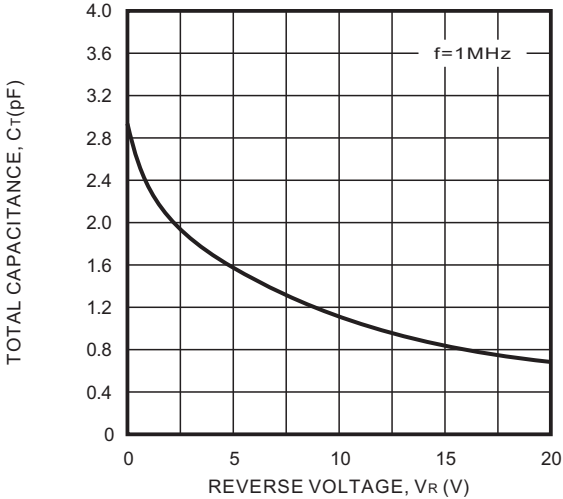
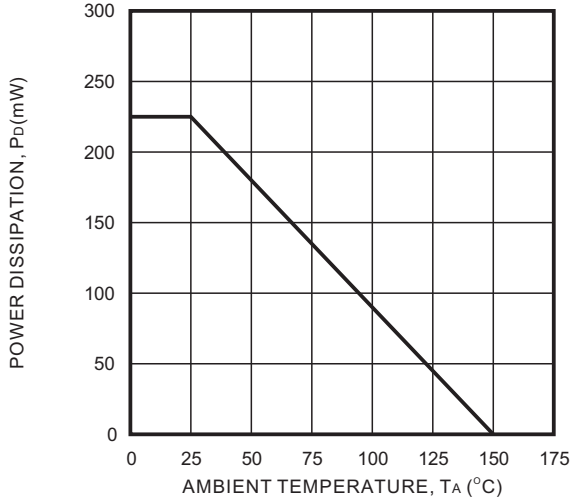
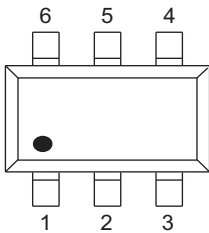
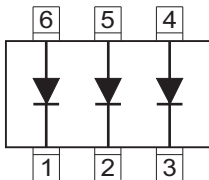


Fig.4 POWER DERATING CURVE



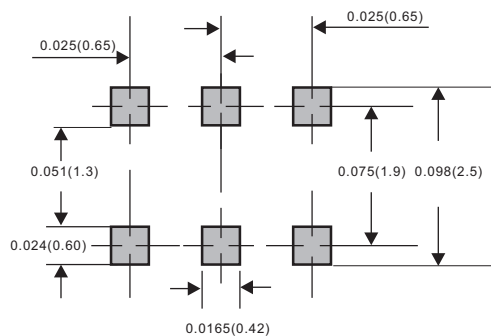
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Pinning information

Type number	Simplified outline	Marking code	Symbol
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Suggested solder pad layout

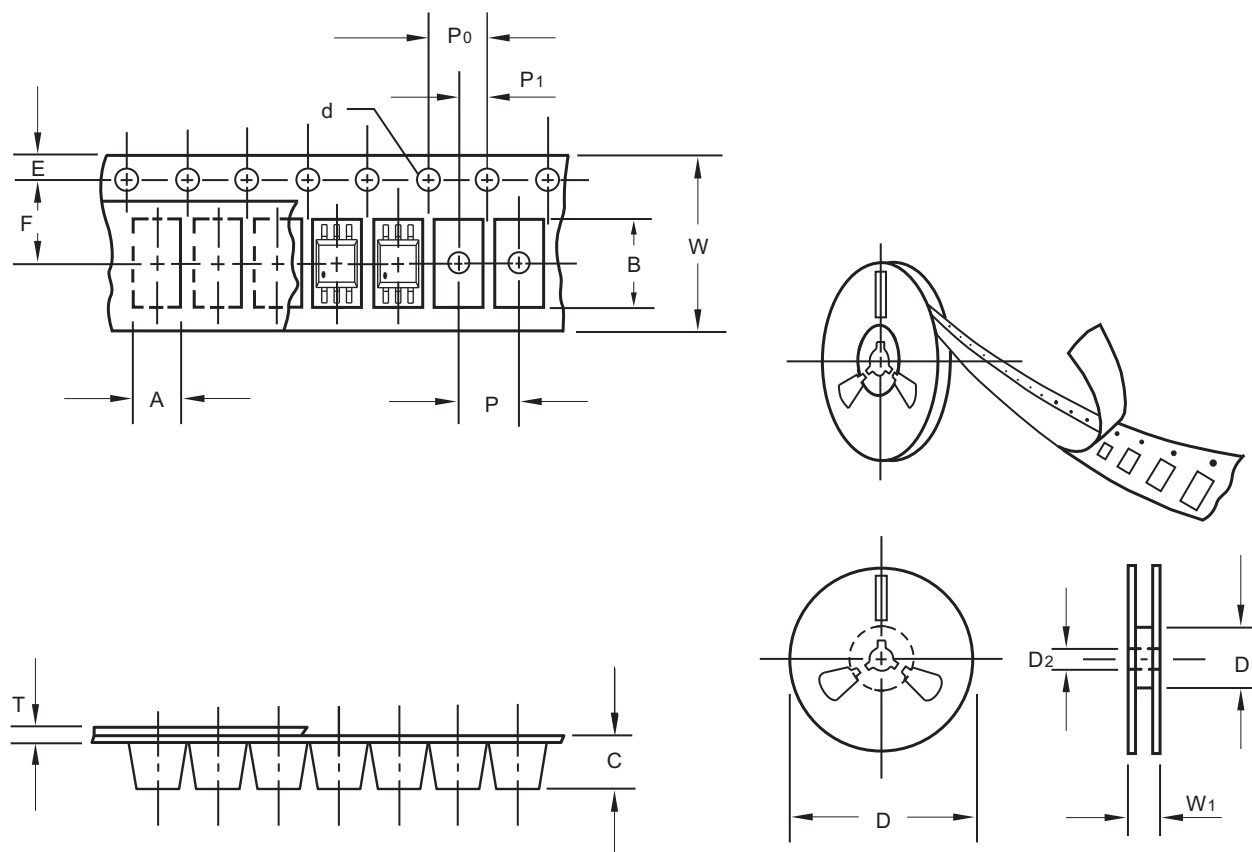
SOT-363



Dimensions in inches and (millimeters)

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Packing information



unit:mm

Item	Symbol	Tolerance	SOT-363
Carrier width	A	0.1	2.25
Carrier length	B	0.1	2.55
Carrier depth	C	0.1	1.20
Sprocket hole	d	0.1	1.50
13" Reel outside diameter	D	2.0	-
13" Reel inner diameter	D1	min	-
7" Reel outside diameter	D	2.0	178.00
7" Reel inner diameter	D1	min	54.40
Feed hole diameter	D2	0.5	13.00
Sprocket hole position	E	0.1	1.75
Punch hole position	F	0.1	3.50
Punch hole pitch	P	0.1	4.00
Sprocket hole pitch	P0	0.1	4.00
Embossment center	P1	0.1	2.00
Overall tape thickness	T	0.1	0.23
Tape width	W	0.3	8.00
Reel width	W1	1.0	11.40

Note: Devices are packed in accordance with EIA standard RS-481-A and specifications listed above.

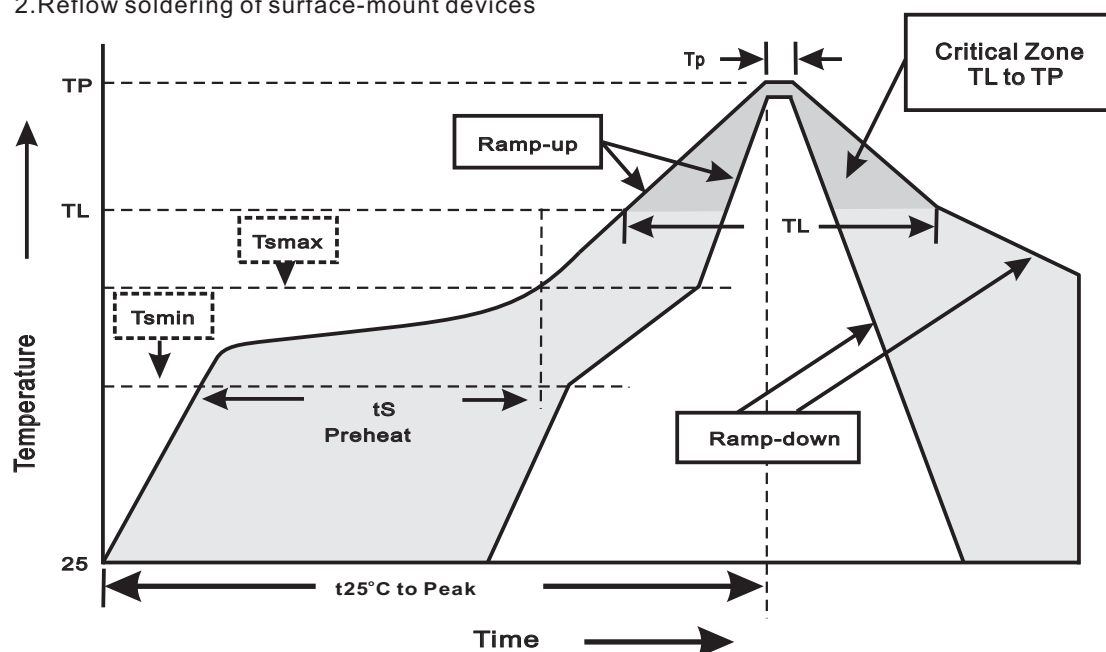
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Reel packing

PACKAGE	REEL SIZE	REEL (pcs)	COMPONENT SPACING (m/m)	BOX (pcs)	INNER BOX (m/m)	REEL DIA, (m/m)	CARTON SIZE (m/m)	CARTON (pcs)	APPROX. GROSS WEIGHT (kg)
SOT-363	7"	3,000	4.0	30,000	183*123*183	178	382*257*387	240,000	9.50

Suggested thermal profiles for soldering processes

- 1.Storage environment: Temperature=5°C~40°C Humidity=55%±25%
- 2.Reflow soldering of surface-mount devices



3.Reflow soldering

Profile Feature	Soldering Condition
Average ramp-up rate(T _L to T _P)	<3°C/sec
Preheat -Temperature Min(T _{smmin}) -Temperature Max(T _{smmax}) -Time(min to max)(t _s)	150°C 200°C 60~120sec
T _{smmax} to T _L -Ramp-upRate	<3°C/sec
Time maintained above: -Temperature(T _L) -Time(t _L)	217°C 60~260sec
Peak Temperature(T _P)	255°C-0/+5°C
Time within 5°C of actual Peak Temperature(t _P)	10~30sec
Ramp-down Rate	<6°C/sec
Time 25°C to Peak Temperature	<6minutes

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High reliability test capabilities

Item Test	Conditions	Reference
1. Solder Resistance	at $260\pm5^{\circ}\text{C}$ for $10\pm2\text{sec.}$ immerse body into solder $1/16''\pm 1/32''$	MIL-STD-750D METHOD-2031
2. Solderability	at $245\pm5^{\circ}\text{C}$ for 5 sec.	MIL-STD-202F METHOD-208
3. High Temperature Reverse Bias	$V_R=80\%$ rate at $T_J=150^{\circ}\text{C}$ for 168 hrs.	MIL-STD-750D METHOD-1038
4. Forward Operation Life	Rated average rectifier current at $T_A=25^{\circ}\text{C}$ for 500hrs.	MIL-STD-750D METHOD-1027
5. Intermittent Operation Life	$T_A = 25^{\circ}\text{C}$, $I_F = I_O$ On state: power on for 5 min. off state: power off for 5 min. on and off for 500 cycles.	MIL-STD-750D METHOD-1036
6. Pressure Cooker	$15P_{SIG}$ at $T_A=121^{\circ}\text{C}$ for 4 hrs.	JESD22-A102
7. Temperature Cycling	-55°C to $+125^{\circ}\text{C}$ dwelled for 30 min. and transferred for 5min. total 10 cycles.	MIL-STD-750D METHOD-1051
8. Forward Surge	Peak Forward Surge Current	MIL-STD-750D METHOD-4066-2
9. Humidity	at $T_A=85^{\circ}\text{C}$, RH=85% for 1000hrs.	MIL-STD-750D METHOD-1021
10. High Temperature Storage Life	at 150°C for 1000 hrs.	MIL-STD-750D METHOD-1031